

PRM028N04D

PFC Device Corporation

40V Single N-Channel MOSFET

Major ratings and characteristics

Characteristics	Values	Units
V_{DS}	40	V
$I_{D}^{6} (T_{C}=25^{\circ}C)$	14	Α
Max. R _{DS(ON)} @V _{GS} =10V	28	mΩ
Max. R _{DS(ON)} @V _{GS} =4.5V	38	mΩ
T _J Operating Junction Temperature	-55 to +150	°C

General Description

The N-Channel enhancement mode power field effect transistor is using trench DMOS technology. This advanced technology has been especially tailored to minimize on-state resistance, provide superior switching performance, and withstand high energy pulse in the avalanche and commutation mode. The device is well suited for high efficiency fast switching applications.

PRM028N04D TO-252 (D-PAK)

Typical Applications

- Charger Adapter
- Power Tools
- LED Lighting

Features

- Max. $R_{DS(ON)}=28m\Omega@V_{GS}=10V$
- Improved dv/dt capability
- Fast switching
- 100% E_{AS} Guaranteed
- Green Device Available

1. Characteristics

Maximum Ratings Characteristics

($T_A = 25$ °C unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	40	V
V_{GS}	Gate-Source Voltage	±20	V
I_D^{5}	Drain Current – Continuous (T _C =25°C)	23.6	Α
ID	Drain Current – Continuous (T _C =100°C)	14.9	А
I _D ⁶	Drain Current – Continuous (T _C =25°C)	14	А
I _{DM}	Drain Current – Pulsed ¹	40	А
E _{AS}	Single Pulse Avalanche Energy ²	5	mJ
I _{AS}	Single Pulse Avalanche Current ²	10	А
D	Power Dissipation (T _C =25°C)	31.2	W
P_D	Power Dissipation – Derate above 25°C	0.25	W/°C
T_{STG}	Storage Temperature Range	-55 to 150	°C
TJ	Operating Junction Temperature Range	-55 to 150	°C

Thermal Characteristics

Symbol	Parameter	Тур.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction to ambient		62	°C/W
$R_{ heta JC}$	Thermal Resistance Junction to Case		4	°C/W



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Electrical Characteristics

($T_J = 25$ °C unless otherwise specified)

Off Characteristics

Symbol	Parameter	Conditions	Min.	Тур.	Max.	Unit
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250uA	40			V
		V _{DS} =40V, V _{GS} =0V, T _J =25°C			1	uA
I _{DSS}	Drain-Source Leakage Current	V _{DS} =40V, V _{GS} =0V, T _J =125°C			250	uA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±20V, V _{DS} =0V			±100	nA

On Characteristics

	R _{DS(ON)} Static Dialit-Source Off-Resistance	V _{GS} =10V, I _D =11A			28	mΩ	
		V _{GS} =4.5V, I _D =5A			38	mΩ	
	$V_{GS(th)}$	Gate Threshold Voltage	V _{GS} =V _{DS} , I _D =250uA	1.0	ł	3.0	V
	g _{fs}	Forward Transconductance	V _{DS} =5V, I _D =11A		17	-	S

Dynamic and switching Characteristics

Q_{g}	Total Gate Charge ^{3, 4}		 10	
Q_{qs}	Gate-Source Charge ^{3, 4}	V _{DS} =20V, V _{GS} =10V, I _D =20A	 2.2	 nC
Q_gd	Gate-Drain Charge ^{3, 4}		 2.5	
$T_{d(on)}$	Turn-On Delay Time ^{3, 4}		 7	
T _r	Turn-On Rise Time ^{3, 4}	V_{DD} =20V, V_{GS} =10V, R_{G} =6 Ω	 18	 ns
$T_{d(off)}$	Turn-Off Delay Time ^{3, 4}	I _D =20A	 13	 115
T_f	Turn-Off Fall Time ^{3, 4}		 3	
C _{iss}	Input Capacitance		 530	
C _{oss}	Output Capacitance	V _{DS} =25V, V _{GS} =0V, f=1MHz	 50	 pF
C_{rss}	Reverse Transfer Capacitance		 35	
R_{g}	Gate resistance	V _{GS} =0V, V _{DS} =0V, f=1MHz	 1.5	 Ω

Drain-Source Diode Characteristics

V _{SD} S	Source to Drain Diode Voltage	V_{GS} =0V, I_S =20A			1.5	V
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Note:

- 1. Repetitive Rating : Pulsed width limited by maximum junction temperature.
- 2. V_{DD} =50V, V_{GS} =10V, L=0.1mH, I_{AS} =10A, R_G =25 Ω , Starting T_J =25 $^{\circ}$ C
- 3. The data tested by pulsed , pulse width \leq 300us , duty cycle \leq 2%.
- 4. Essentially independent of operating temperature.
- 5. Silicon limited.
- 6. Package limited.

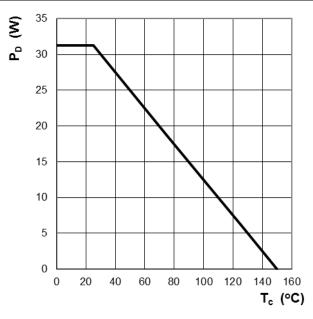


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2. Characteristics Curves

Ratings and Characteristics Curves

(T_A = 25°C unless otherwise specified)



25 20 15 10 5 0 25 50 75 100 125 150 T_c (°C)

Figure 1: Power Dissipation

Figure 2: Continuous Drain Current vs. T_C

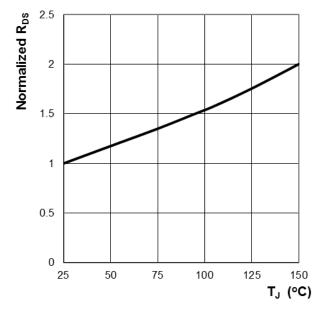


Figure 3: Normalized R_{DS(ON)} vs. T_J

Figure 4: Normalized BV_{DSS} vs. T_J



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Ratings and Characteristics Curves

(T_A = 25° ∪ unless otherwise specified)

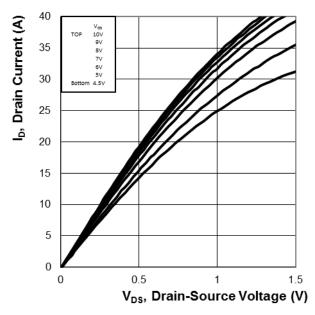


Figure 5: On-Region Characteristics

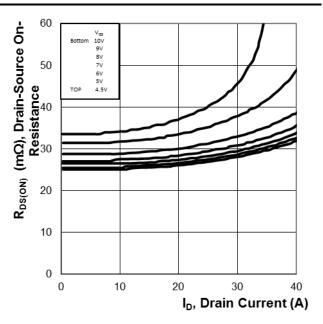


Figure 6: Typ. R_{DS} Variation vs. I_D and V_{GS}

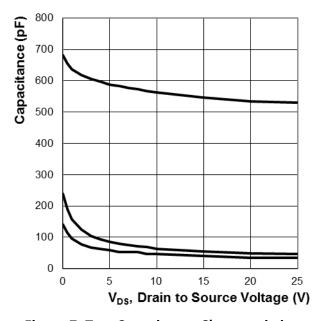


Figure 7: Typ. Capacitance Characteristics

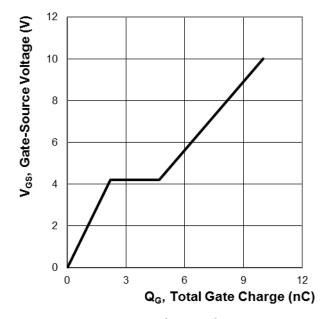


Figure 8: Typ. Gate Charge Characteristics



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Ratings and Characteristics Curves

(T_A = 25°C unless otherwise specified)

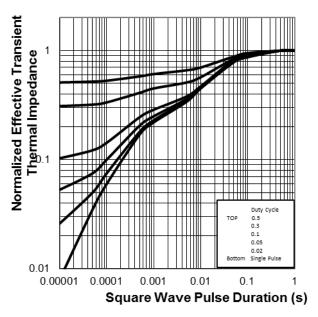


Figure 9: Normalized Thermal Transient Impedance, Junction-to-Case

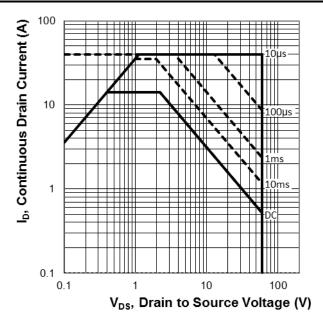


Figure 10: Maximum Safe Operation Area



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3. Marking information

Top Marking Rule

PFC PRM
028N04D
YYWW ABSH

PRM028N04D = Product Type Marking Code

YYWW = Date Code

YY = Last two digits of year

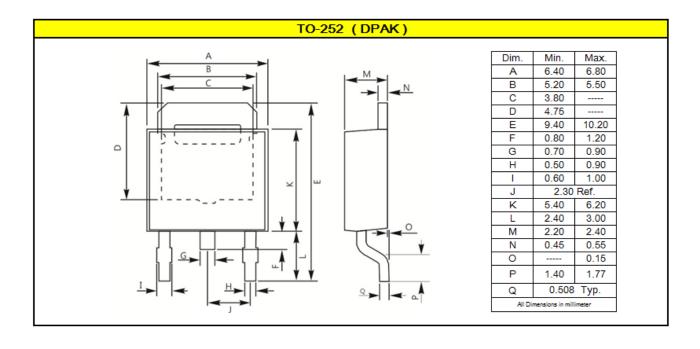
WW = Week code

ABS = Assembly code

H = Halogen Free (N/A = common molding compound)

4. Package information

Package Outline Dimensions millimeters





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5. Ordering information

Part Number	Package	Delivery mode
PRM028N04D	TO-252 (D-PAK)	2500 pcs / 13" diameter reel

Mechanical

Molder Plastic: UL Flammability Classification Rating 94V-0

Device Weight: 0.01 ounces (0.3grams) - TO-252 (D-PAK)

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